Analog Power AM4302N

## N-Channel 30-V (D-S) MOSFET

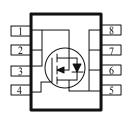
These miniature surface mount MOSFETs utilize High Cell Density process. Low r<sub>DS(on)</sub> assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

•	Low r <sub>DS(on)</sub> Provides Higher Efficiency and
	Extends Battery Life

- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}m(\Omega)$	$I_{D}(A)$		
30	$26 @ V_{GS} = 4.5V$	9.0		
30	$50 @ V_{GS} = 2.5V$	6.5		





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter			Limit	Units	
Drain-Source Voltage			30	V	
Gate-Source Voltage			±12	V	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$	],	±9.0		
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1 <sub>D</sub>	±7.3	A	
Pulsed Drain Current <sup>b</sup>			±50		
Continuous Source Current (Diode Conduction) <sup>a</sup>			2.3	A	
Decree Discipation <sup>a</sup>	$T_A=25^{\circ}C$	D	3.1	W	
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	T D	2.2		
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
M	t <= 10 sec	D	50	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{ heta JA}$	92	°C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

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D	G 1 1 T 4 G 199	Limits			**		
Parameter	Symbol Test Conditions		Min	Тур	Max	Unit	
Static	-						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_D = 250 \text{ uA}$	30			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1.0		1.5	l v	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	<sup>1</sup> DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = \pm 12 \text{ V}$	20			A	
D : C O D : A		$V_{GS} = 4.5 \text{ V}, I_D = 9 \text{ A}$	20		26	0	
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, I_D = 6.5 \text{ A}$			50	mΩ	
Forward Tranconductance <sup>A</sup>	$g_{ m fs}$	$V_{DS} = 15 \text{ V}, I_{D} = 9 \text{ A}$		40		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 2.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	V - 15 V V - 4 5 V		5.5			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		1.0		nC	
Gate-Drain Charge	$Q_{gd}$	$I_D = 9 A$		1.4		1	
Gate Resistance	$R_{G}$			1.3		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			20			
Rise Time	$t_{\rm r}$	$V_{DD} = 25 \text{ V}, R_L = 25 \Omega, I_D = 1 \text{ A},$		9		1	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		70		nS	
Fall-Time	$t_{\rm f}$			20			
Source-Ddrain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 2.3 \text{ A, Di/Dt} = 100 \text{ A/uS}$		41		1	

## Notes

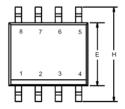
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

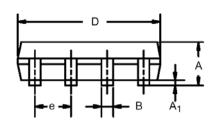
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## Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INC	HES
Dim	Min	Max	Min	Max
Α	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
В	0.35	0.51	0.014	0.020
С	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

